

2N4223 2N4224

CASE 20-03, STYLE 3
TO-72 (TO-206AF)

JFET
VHF AMPLIFIER
N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	-30	Vdc
Drain Current	I_D	20	mA _{dc}
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.0	mW mW/ $^\circ\text{C}$
Operating and Junction Temperature Range	T_J	-65 to +175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = -10 \mu\text{A}_{dc}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	-30	—	Vdc
Gate Reverse Current ($V_{GS} = -20 \text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	—	-0.25	nA _{dc}
		2N4223	—	
($V_{GS} = -20 \text{ Vdc}$, $V_{DS} = 0$, $T_A = 100^\circ\text{C}$)	2N4223 2N4224	—	-250	
		—	-500	
Gate Source Cutoff Voltage ($I_D = 0.25 \text{ mA}_{dc}$, $V_{DS} = 15 \text{ Vdc}$) ($I_D = 0.50 \text{ mA}_{dc}$, $V_{DS} = 15 \text{ Vdc}$)	$V_{GS(off)}$	-1.2	-8.0	Vdc
		—	-8.0	
Gate Source Voltage ($I_D = 0.3 \text{ mA}_{dc}$, $V_{DS} = 15 \text{ Vdc}$) ($I_D = 0.2 \text{ mA}_{dc}$, $V_{DS} = 15 \text{ Vdc}$)	V_{GS}	-1.0	-7.0	Vdc
		-1.0	-7.5	
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current* ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	3.0	18	mA _{dc}
		2.0	20	
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ kHz}$)*	$ y_{fs} $	3000	7000	μmhos
		2N4223	2000	
	2N4224	—	—	
($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 200 \text{ MHz}$)	2N4223 2N4224	2700 1700	— —	
Input Conductance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 200 \text{ MHz}$)	$\text{Re}(y_{is})$	—	800	μmhos
Output Conductance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 200 \text{ MHz}$)	$\text{Re}(y_{os})$	—	200	μmhos
Input Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{iss}	—	6.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{rss}	—	2.0	pF

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ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
FUNCTIONAL CHARACTERISTICS				
Noise Figure ($V_{DS} = 15\text{ Vdc}$, $V_{GS} = 0$, $R_S = 1.0\text{ k ohm}$, $f = 200\text{ MHz}$)	NF	—	5.0	dB
Small-Signal Power Gain Common Source ($V_{DS} = 15\text{ Vdc}$, $V_{GS} = 0$, $f = 200\text{ MHz}$)	G_{ps}	10	—	dB

*Pulse Test: Pulse Width $\leq 630\text{ ms}$, Duty Cycle $\leq 10\%$.

FIGURE 1—NOISE FIGURE AND POWER GAIN TEST CIRCUIT

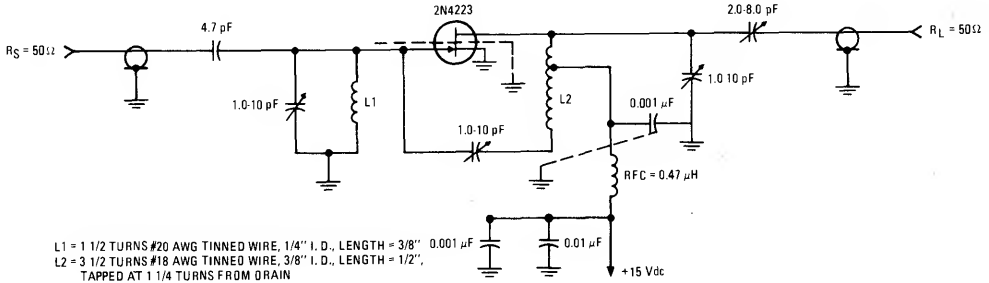


FIGURE 2 — DRAIN CURRENT versus GATE-SOURCE VOLTAGE

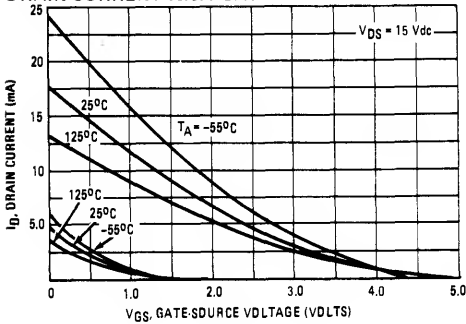


FIGURE 3 — TEMPERATURE COEFFICIENT FOR DRAIN CURRENT

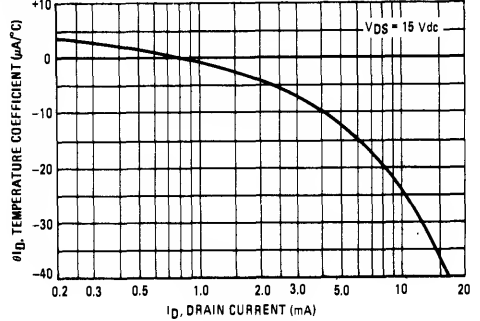


FIGURE 4 — FORWARD TRANSFER ADMITTANCE versus GATE-SOURCE VOLTAGE

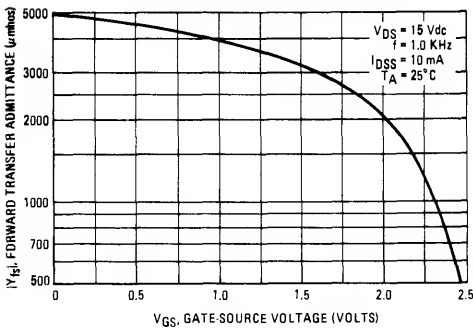


FIGURE 5 — TEMPERATURE COEFFICIENT FOR Y_{fs} versus DRAIN CURRENT

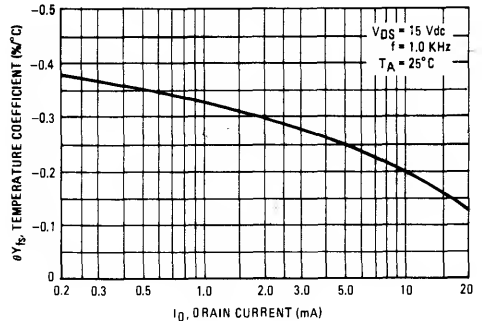


FIGURE 6 – CAPACITANCES

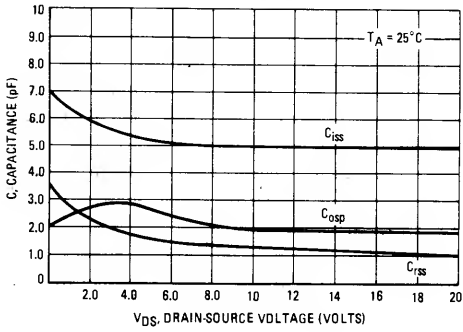


FIGURE 7 – COMMON SOURCE NOISE FIGURE versus SOURCE RESISTANCE

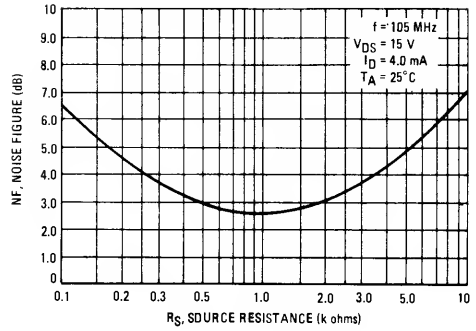


FIGURE 8 – INPUT ADMITTANCE versus FREQUENCY

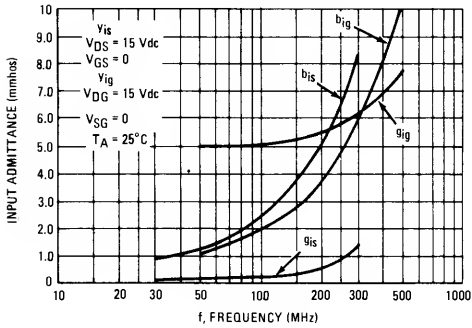


FIGURE 9 – FORWARD TRANSFER ADMITTANCE versus FREQUENCY

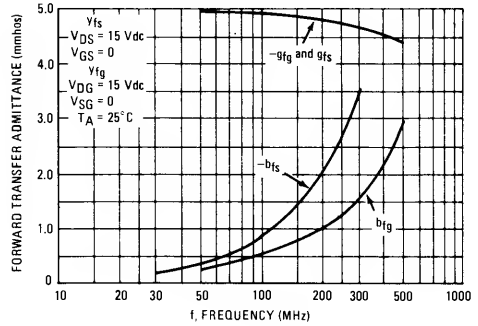


FIGURE 10 – OUTPUT ADMITTANCE versus FREQUENCY

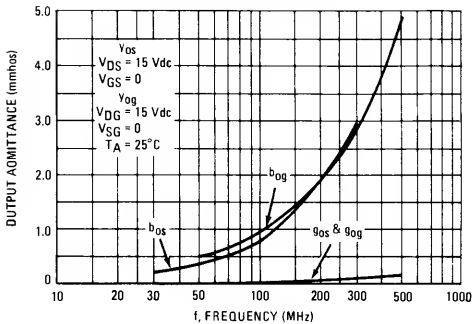
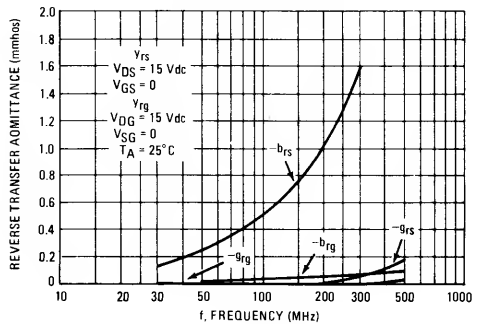


FIGURE 11 – REVERSE TRANSFER ADMITTANCE versus FREQUENCY



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FIGURE 12 – POWER GAIN versus FREQUENCY

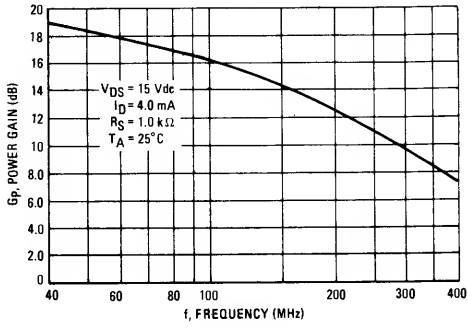


FIGURE 13 – COMMON SOURCE NOISE FIGURE versus FREQUENCY

